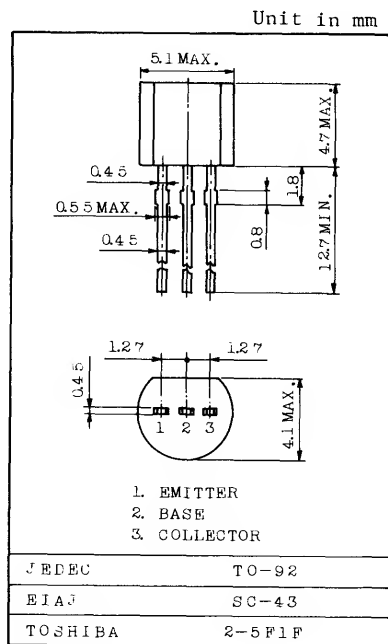


FOR GENERAL PURPOSE USE SWITCHING AND AMPLIFIER APPLICATIONS.

FEATURES:

- . Low Leakage Current  
:  $I_{CEV} = -50\text{nA (Max.)}$ ,  $I_{BEV} = 50\text{nA (Max.)}$   
@  $V_{CE} = -30\text{V}$ ,  $V_{BE} = 3\text{V}$
- . Excellent DC Current Gain Linearity
- . Low Saturation Voltage  
:  $V_{CE(sat)} = -0.4\text{V (Max.)}$  @  $I_C = -50\text{mA}$ ,  $I_B = -5\text{mA}$
- . Low Collector Output Capacitance  
:  $C_{ob} = 4.5\text{pF (Max.)}$  @  $V_{CB} = -5\text{V}$
- . Complementary to 2N3903



Weight : 0.21g

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
* Collector-Base Voltage	$V_{CBO}$	-40	V
* Collector-Emitter Voltage	$V_{CEO}$	-40	V
* Emitter-Base Voltage	$V_{EBO}$	-5	V
* Collector Current	$I_C$	-200	mA
Base Current	$I_B$	-50	mA
* Collector Power Dissipation ( $T_a = 25^\circ\text{C}$ ) Derate Linearly $25^\circ\text{C}$	$P_C$	350	mW
		2.8	mW/ $^\circ\text{C}$
* Collector Power Dissipation ( $T_c = 25^\circ\text{C}$ ) Detate Linearly $25^\circ\text{C}$	$P_C$	1.0	W
		8	mW/ $^\circ\text{C}$
* Thermal Resistance (Junction to Ambient)	$R_{th(j-a)}$	357	$^\circ\text{C/W}$
* Thermal Resistance (Junction to Case)	$R_{th(j-c)}$	125	$^\circ\text{C/W}$
* Junction Temperature	$T_j$	150	$^\circ\text{C}$
* Storage Temperature Range	$T_{stg}$	-55 ~ 150	$^\circ\text{C}$

\*In Accordance with JEDEC registration data.

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
※	Collector Cut-off Current	ICEV	VCE=-30V, VBE=3V	-	-	-50	nA	
※	Base Cut-off Current	IBEV	VCE=-30V, VBE=3V	-	-	50	nA	
※	Collector-Base Breakdown Voltage	V(BR)CBO	IC=-10μA, IE=0	-40	-	-	V	
※	Collector-Emitter Breakdown Voltage	V(BR)CEO	IC=-1mA, IB=0	-40	-	-	V	
※	Emitter-Base Breakdown Voltage	V(BR)EBO	IE=-10μA, IC=0	-5	-	-	V	
※	DC Current Gain	hFE(1)	VCE=-1V, IC=-0.1mA	30	-	-		
		hFE(2)	VCE=-1V, IC=-1mA	40	-	-		
		hFE(3)	VCE=-1V, IC=-10mA	50	-	150		
		hFE(4)	VCE=-1V, IC=-50mA	30	-	-		
		hFE(5)	VCE=-1V, IC=-100mA	15	-	-		
※	Collector-Emitter Saturation Voltage	VCE(sat)1	IC=-10mA, IB=-1mA	-	-	-0.25	V	
		VCE(sat)2	IC=-50mA, IB=-5mA	-	-	-0.4		
※	Base-Emitter Saturation Voltage	VBE(sat)1	IC=-10mA, IB=-1mA	-0.65	-	-0.85	V	
		VBE(sat)2	IC=-50mA, IB=-5mA	-	-	-0.95		
※	Transition Frequency	fT	VCE=-20V, IC=-10mA f=100MHz	200	-	-	MHz	
※	Collector Output Capacitance	COB	VCB=-5V, IE=0, f=1MHz	-	-	4.5	pF	
※	Input Capacitance	CIB	VBE=-0.5V, IC=0 f=1MHz	-	-	10	pF	
※	Input Impedance	hie	VCE=-10V, IC=-1mA f=1kHz	0.5	-	8	kΩ	
※	Voltage Feedback Ratio	hRE		0.1	-	5	×10 <sup>-4</sup>	
※	Small-Signal Current Gain	hFE		50	-	200		
※	Collector Output Admittance	hoe		1.0	-	40	μS	
※	Noise Figure	NF		VCE=-5V, IC=-0.1mA Rg=1kΩ, f=10Hz ~ 15.7kHz	-	-	5	dB
※	Switching Time	Delay Time	td(ON)		-	-	35	ns
		Rise Time	tr		-	-	35	
		Storage Time	tstg		-	-	200	
		Fall Time	tf		-	-	60	

In accordance with JEDEC registration data.